

## Amendments to the Claims

### Listing of Claims:

Claims 10-12 (canceled)

Claim 13 (currently amended) A method for forming an embedded resistor comprising the steps of:

depositing a thin film cermet material approximately 1000 angstroms thick comprising  $M_xSi_yO_z$ ;

where M = W or Ta

said deposition onto a substrate is performed by co-sputtering of two targets: a first target of W or Ta and a second target of  $SiO_2$ ;

wherein sputtering of said  $SiO_2$  target is r.f. sputtering; and,  
deposition of the film on a substrate includes the steps of utilizing r.f. and d.c. magnetron sputtering with argon gas; and controlling the resistivity and TCR of the thin film cermet material by varying the sputtering power and pressure to obtain Rs and TCR values in accordance with the following table:

Rs (ohms/Square)	TCR (ppm/C)	Pressure (mTorr)	Power (kW)
250	$\leq -200$	10	2.0
400	$\leq -220$	14	1.0
800	$\leq -260$	14	0.4
1500	$\leq -400$	18	0.4

Claim 14 (canceled)

Claim 15 (canceled)

Claim 16 (withdrawn) In the method of testing cermet thin film resistors having a resistivity of  $\sim 0.2-1.5 \times 10^{-2} \Omega\text{-cm}$ :

providing 1000 cycles of thermal shock testing over the range of -55 to 125°C to provide  $\leq 0.2\%$  tracking for a square resistor pair.

Claim 17 ( withdrawn) In the method of testing cermet thin film resistors having a resistivity of  $\sim 0.2-1.5 \times 10^{-2} \Omega\text{-cm}$ :

providing 1000 cycles of thermal shock testing over the range of -55 to 125°C to provide  $\leq 0.2\%$  tracking for a square resistor pair to provide  $\leq 0.02\%$  tracking for other resistor pairs..